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Data Sheet

LED Chip Infrared

EOLC-770-11

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Radiation	Type	Electrodes
Infrared	AlGaAs, DDH	P (anode) up

Typ. thickness: 150±30 μm
 Anode: gold alloy, thickness 1.5 μm
 Cathode: gold alloy, thickness 0.5 μm, structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.5	2	V
Forward voltage	I _F =350 mA	V _F		1.8		V
Reverse voltage	I _R =100 μA	V _R	5			V
Radiant power*	I _F =20 mA	Φ _e	2.5	3.5		mW
Radiant power*	I _F =350 mA	Φ _e		70		mW
Peak wavelength	I _F =350 mA	λ _p	760	770	780	nm
FWHM	I _F =350 mA	Δλ _{0.5}		30		nm
Switching time	I _F =20 mA	t _r , t _f		15		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 016



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.